Vanya Darakchieva

List of Publications by Year
in descending order

163 papers	4,473 citations	126708 33 h-index	123241 61 g-index
167 all docs	167 docs citations	167 times ranked	5021 citing authors

#	Article	IF	Citations
1	Infrared dielectric functions and phonon modes of high-quality ZnO films. Journal of Applied Physics, 2003, 93, 126-133.	1.1	590
2	On the organization and thermal behavior of functional groups on Ti ₃ C ₂ MXene surfaces in vacuum. 2D Materials, 2018, 5, 015002.	2.0	219
3	2D Transition Metal Carbides (MXenes) for Carbon Capture. Advanced Materials, 2019, 31, e1805472.	11.1	184
4	Tailoring Structure, Composition, and Energy Storage Properties of MXenes from Selective Etching of Inâ€Plane, Chemically Ordered MAX Phases. Small, 2018, 14, e1703676.	5.2	174
5	Two-dimensional electron gas density in Al1â^'xInxN/AlN/GaN heterostructures (0.03â‰¤xâ‰¤0.23). Journal of Applied Physics, 2008, 103, .	1.1	154
6	Anisotropy, phonon modes, and free charge carrier parameters in monoclinic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Î²</mml:mi></mml:math>-gallium oxide single crystals. Physical Review B, 2016, 93, .	1.1	147
7	Band-to-band transitions, selection rules, effective mass, and excitonic contributions in monoclinic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2017, 96, .	1.1	117
8	How Much Oxygen Can a MXene Surface Take Before It Breaks?. Advanced Functional Materials, 2020, 30, 1909005.	7.8	111
9	On the lattice parameters of GaN. Applied Physics Letters, 2007, 91, .	1.5	101
10	Anisotropic strain and phonon deformation potentials in GaN. Physical Review B, 2007, 75, .	1.1	99
11	Very high growth rate of 4H-SiC epilayers using the chlorinated precursor methyltrichlorosilane (MTS). Journal of Crystal Growth, 2007, 307, 334-340.	0.7	83
12	High-quality bulk a-plane GaN sliced from boules in comparison to heteroepitaxially grown thick films on r-plane sapphire. Applied Physics Letters, 2006, 89, 051914.	1.5	78
13	Electronic and optical characterization of 2D Ti₂C and Nb₂C (MXene) thin films. Journal of Physics Condensed Matter, 2019, 31, 165301.	0.7	74
14	Conductive polymer nanoantennas for dynamic organic plasmonics. Nature Nanotechnology, 2020, 15, 35-40.	15.6	70
15	Properties of nonpolar a-plane GaN films grown by HVPE with AlN buffers. Journal of Crystal Growth, 2005, 281, 55-61.	0.7	66
16	Strain-related structural and vibrational properties of thin epitaxialAlNlayers. Physical Review B, 2004, 70, .	1.1	59
17	Effects of strain and composition on the lattice parameters and applicability of Vegardâ€™s rule in Al-rich Al1â^'xInxN films grown on sapphire. Journal of Applied Physics, 2008, 103, .	1.1	54
18	Deformation potentials of the E1(TO) and E2 modes of InN. Applied Physics Letters, 2004, 84, 3636-3638.	1.5	47

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19	Lattice parameters, deviations from Vegardâ€™s rule, and E2 phonons in InAlN. Applied Physics Letters, 2008, 93, .	1.5	44
20	Epitaxial CVD growth of sp²â€hybridized boron nitride using aluminum nitride as buffer layer. Physica Status Solidi - Rapid Research Letters, 2011, 5, 397-399.	1.2	44
21	Temperature dependent effective mass in AlGaN/GaN high electron mobility transistor structures. Applied Physics Letters, 2012, 101, .	1.5	44
22	Electron effective mass in Sn-doped monoclinic single crystal Î²-gallium oxide determined by mid-infrared optical Hall effect. Applied Physics Letters, 2018, 112, .	1.5	43
23	Y_xAl_{1â^'x}N thin films. Journal Physics D: Applied Physics, 2012, 45, 422001.	1.3	42
24	Advanced Terahertz Frequency-Domain Ellipsometry Instrumentation for In Situ and Ex Situ Applications. IEEE Transactions on Terahertz Science and Technology, 2018, 8, 257-270.	2.0	42
25	Free electron behavior in InN: On the role of dislocations and surface electron accumulation. Applied Physics Letters, 2009, 94, 022109.	1.5	41
26	Optical Hall effectâ€”model description: tutorial. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 2016, 33, 1553.	0.8	40
27	Lattice parameters of GaN layers grown on a-plane sapphire: Effect of in-plane strain anisotropy. Applied Physics Letters, 2003, 82, 703-705.	1.5	39
28	Optical Hall Effect in Hexagonal InN. Journal of Electronic Materials, 2008, 37, 611-615.	1.0	39
29	Phonon mode behavior in strained wurtziteAlNâ•GaNsuperlattices. Physical Review B, 2005, 71, .	1.1	38
30	Strong Plasmonâ€“Exciton Coupling with Directional Absorption Features in Optically Thin Hybrid Nanohole Metasurfaces. ACS Photonics, 2018, 5, 4046-4055.	3.2	37
31	Anisotropy of the Î“-point effective mass and mobility in hexagonal InN. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1854-1857.	0.8	36
32	Hydrogen in InN: A ubiquitous phenomenon in molecular beam epitaxy grown material. Applied Physics Letters, 2010, 96, .	1.5	36
33	On the anomalous optical conductivity dispersion of electrically conducting polymers: ultra-wide spectral range ellipsometry combined with a Drudeâ€“Lorentz model. Journal of Materials Chemistry C, 2019, 7, 4350-4362.	2.7	36
34	Tunable Structural Color Images by UVâ€Patterned Conducting Polymer Nanofilms on Metal Surfaces. Advanced Materials, 2021, 33, e2102451.	11.1	34
35	Visible to vacuum ultraviolet dielectric functions of epitaxial graphene on 3C and 4H SiC polytypes determined by spectroscopic ellipsometry. Applied Physics Letters, 2012, 101, .	1.5	33
36	Deformation potentials of the E1(TO) mode in AlN. Applied Physics Letters, 2002, 80, 2302-2304.	1.5	32

#	Article	IF	Citations
37	Structural characteristics and lattice parameters of hydride vapor phase epitaxial GaN free-standing quasisubstrates. Journal of Applied Physics, 2005, 97, 013517.	1.1	32
38	Electrical Tuning of Plasmonic Conducting Polymer Nanoantennas. Advanced Materials, 2022, 34, e2107172.	11.1	32
39	Elastic constants, composition, and piezoelectric polarization in In<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Al<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â”</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>N: From ab initio calculations to experimental implications for the applicability of Vegard's rule.	1.1	31
40	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. Applied Physics Letters, 2006, 88, 141909.	1.5	30
41	Electron effective mass in Al0.72Ga0.28N alloys determined by mid-infrared optical Hall effect. Applied Physics Letters, 2013, 103, .	1.5	30
42	Morphological and electronic properties of epitaxial graphene on SiC. Physica B: Condensed Matter, 2014, 439, 54-59.	1.3	29
43	Large-area microfocal spectroscopic ellipsometry mapping of thickness and electronic properties of epitaxial graphene on Si- and C-face of 3C-SiC(111). Applied Physics Letters, 2013, 102, .	1.5	28
44	Growth and separation related properties of HVPE-GaN free-standing films. Journal of Crystal Growth, 2002, 246, 207-214.	0.7	27
45	The anisotropic quasi-static permittivity of single-crystal Î² -Ga2O3 measured by terahertz spectroscopy. Applied Physics Letters, 2020, 117, .	1.5	27
46	Dielectric function tensor (1.5 eV to 9.0 eV), anisotropy, and band to band transitions of monoclinic Î² -(AlxGa1â€“x)2O3 (x â‰ˆ 0.21) films. Applied Physics Letters, 2019, 114, .	1.5	25
47	Very high crystalline quality of thick 4Hâ€SiC epilayers grown from methyltrichlorosilane (MTS). Physica Status Solidi - Rapid Research Letters, 2008, 2, 188-190.	1.2	24
48	Electron accumulation at nonpolar and semipolar surfaces of wurtzite InN from generalized infrared ellipsometry. Applied Physics Letters, 2009, 95, 202103.	1.5	24
49	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. Carbon, 2017, 116, 722-732.	5.4	23
50	In-situ terahertz optical Hall effect measurements of ambient effects on free charge carrier properties of epitaxial graphene. Scientific Reports, 2017, 7, 5151.	1.6	23
51	Structural and optical analysis ofÎ²â€™FeSi2thin layers prepared by ion-beam synthesis and solid-state reaction. Physical Review B, 2000, 62, 13057-13063.	1.1	22
52	Infrared to vacuum-ultraviolet ellipsometry and optical Hall-effect study of free-charge carrier parameters in Mg-doped InN. Journal of Applied Physics, 2013, 113, .	1.1	22
53	Structural anisotropy of nonpolar and semipolar InN epitaxial layers. Journal of Applied Physics, 2010, 108, .	1.1	21
54	Longitudinal phonon plasmon mode coupling in Î² -Ga2O3. Applied Physics Letters, 2019, 114, .	1.5	21

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55	Hydride vapor-phase epitaxial GaN thick films for quasi-substrate applications: Strain distribution and wafer bending. Journal of Electronic Materials, 2004, 33, 389-394.	1.0	20
56	Lattice parameters of bulk GaN fabricated by halide vapor phase epitaxy. Journal of Crystal Growth, 2008, 310, 959-965.	0.7	19
57	Cavity-enhanced optical Hall effect in two-dimensional free charge carrier gases detected at terahertz frequencies. Optics Letters, 2015, 40, 2688.	1.7	19
58	Residual strain in HVPE GaN free-standing and re-grown homoepitaxial layers. Physica Status Solidi A, 2003, 195, 516-522.	1.7	18
59	Two-domain formation during the epitaxial growth of GaN (0001) on c-plane Al2O3 (0001) by high power impulse magnetron sputtering. Journal of Applied Physics, 2011, 110, .	1.1	18
60	Direct graphene growth on Co₃O₄(111) by molecular beam epitaxy. Journal of Physics Condensed Matter, 2012, 24, 072201.	0.7	18
61	Polarization Selection Rules for Inter-Landau-Level Transitions in Epitaxial Graphene Revealed by the Infrared Optical Hall Effect. Physical Review Letters, 2013, 111, 077402.	2.9	18
62	Thermal conductivity of ultra-wide bandgap thin layers â€“ High Al-content AlGaN and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.svg"><mml:mrow><mml:mi mathvariant="bold-italic">Î²</mml:mi></mml:mrow></mml:math>-Ga2O3. Physica B: Condensed Matter, 2020, 579, 411810.	1.3	18
63	Ion beam synthesis of Î²-FeSi2. Vacuum, 2000, 58, 415-419.	1.6	17
64	Effect of nitrogen on the GaAs0.9â^'xNxSb0.1 dielectric function from the near-infrared to the ultraviolet. Applied Physics Letters, 2010, 97, 201903.	1.5	17
65	Structure and properties of phosphorus-carbide thin solid films. Thin Solid Films, 2013, 548, 247-254.	0.8	17
66	Epitaxial growth of Î²-Ga2O3 by hot-wall MOCVD. AIP Advances, 2022, 12, .	0.6	17
67	Influence of grain size on the optical conductivity of Î²-FeSi2 layers. Vacuum, 2002, 69, 425-429.	1.6	16
68	Growth of GaN ona-plane sapphire: in-plane epitaxial relationships and lattice parameters. Physica Status Solidi (B): Basic Research, 2003, 240, 318-321.	0.7	16
69	Phonons and free-carrier properties of binary, ternary, and quaternary group-III nitride layers measured by Infrared Spectroscopic Ellipsometry. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1750-1769.	0.8	16
70	Infrared ellipsometry and Raman studies of hexagonal InN films: correlation between strain and vibrational properties. Superlattices and Microstructures, 2004, 36, 573-580.	1.4	16
71	Polar and nonpolar GaN grown by HVPE: Preferable substrates for nitride-based emitting devices. Physica Status Solidi A, 2004, 201, 2265-2270.	1.7	16
72	Effect of Mg doping on the structural and free-charge carrier properties of InN films. Journal of Applied Physics, 2014, 115, 163504.	1.1	16

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73	Structural properties and dielectric function of graphene grown by high-temperature sublimation on 4H-SiC(000-1). Journal of Applied Physics, 2015, 117, .	1.1	16
74	Role of impurities and dislocations for the unintentional n-type conductivity in InN. Physica B: Condensed Matter, 2009, 404, 4476-4481.	1.3	15
75	Standardâ€free composition measurements of Al_x In_{1â€“x}N by lowâ€loss electron energy loss spectroscopy. Physica Status Solidi - Rapid Research Letters, 2011, 5, 50-52.	1.2	15
76	Enhanced dynamic annealing and optical activation of Eu implanted a-plane GaN. Europhysics Letters, 2012, 97, 68004.	0.7	15
77	Assessing structural, free-charge carrier, and phonon properties of mixed-phase epitaxial films: The case of InN. Physical Review B, 2014, 90, .	1.1	15
78	Properties of twoâ€dimensional electron gas in AlGaN/GaN HEMT structures determined by cavityâ€enhanced THz optical Hall effect. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 369-373.	0.8	15
79	Infrared dielectric functions, phonon modes, and free-charge carrier properties of high-Al-content AlxGa1â^'xN alloys determined by mid infrared spectroscopic ellipsometry and optical Hall effect. Journal of Applied Physics, 2017, 121, .	1.1	14
80	Mg-doping and free-hole properties of hot-wall MOCVD GaN. Journal of Applied Physics, 2022, 131, .	1.1	14
81	Phonon order and reststrahlen bands of polar vibrations in crystals with monoclinic symmetry. Physical Review B, 2019, 99, .	1.1	13
82	Strain and stress relationships for optical phonon modes in monoclinic crystals with <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub><mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> as an example. Physical Review B, 2020, 102, .	1.1	13
83	Nonpolara-plane HVPE GaN: growth and in-plane anisotropic properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2027-2031.	0.8	12
84	Infrared dielectric functions and optical phonons of wurtzite Y_xAl_{1â^'x}N (0â€‰â€‰â©½â€‰â€‰xâ€‰â€‰â©½â€‰â€‰0.22). Journal Physics 48, 415102.	1.3	12
85	Infrared generalized ellipsometry on nonâ€polar and superlattice groupâ€III nitride films: strain and phonon anisotropy. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 905-913.	0.8	11
86	Bandgap Engineering and Optical Constants of YxAl1-xN Alloys. Japanese Journal of Applied Physics, 2013, 52, 08JM02.	0.8	11
87	Stress evolution during growth of GaN (0001)/Al₂O₃(0001) by reactive dc magnetron sputter epitaxy. Journal Physics D: Applied Physics, 2014, 47, 145301.	1.3	11
88	Tunable cavity-enhanced terahertz frequency-domain optical Hall effect. Review of Scientific Instruments, 2020, 91, 083903.	0.6	11
89	Optical phonon modes, static and high-frequency dielectric constants, and effective electron mass parameter in cubic In2O3. Journal of Applied Physics, 2021, 129, .	1.1	11
90	Phonon-boundary scattering and thermal transport in AlxGa1â^'xN: Effect of layer thickness. Applied Physics Letters, 2020, 117, .	1.5	11

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91	Defect Reduction in HVPE Growth of GaN and Related Optical Spectra. Physica Status Solidi A, 2001, 183, 197-203.	1.7	10
92	Photoluminescence in n-doped In0.1Ga0.9N/In0.01Ga0.99N multiple quantum wells. MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	10
93	Effect of anisotropic strain on phonons in a-plane and c-plane GaN layers. Journal of Crystal Growth, 2007, 300, 233-238.	0.7	10
94	Al1â^'xInxN/GaN bilayers: Structure, morphology, and optical properties. Physica Status Solidi (B): Basic Research, 2010, 247, 1740-1746.	0.7	10
95	Decoupling and ordering of multilayer graphene on C-face 3C-SiC(111). Applied Physics Letters, 2016, 109,	1.5	10
96	Infrared dielectric functions and Brillouin zone center phonons of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î±</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub><mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> compared to <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Î±</mml:mi></mml:math> - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:m. Physical Review Materials, 2	0.9	10
97	Free-Standing HVPE-GaN Quasi-Substrates: Impurity and Strain Distributions. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 209-213.	0.8	9
98	Photoluminescence of GaN/AlN superlattices grown by MOCVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2345-2348.	0.8	9
99	Very high epitaxial growth rate of SiC using MTS as chloride-based precursor. Surface and Coatings Technology, 2007, 201, 8931-8934.	2.2	9
100	Free electron properties and hydrogen in InN grown by MOVPE. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1179-1182.	0.8	9
101	Lattice dynamics of orthorhombic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>NdGaO</mml:mi><mml:mn>3</mml:mn></mml:msub></ Physical Review B, 2019, 99, .	1.1	9
102	Doped semiconducting polymer nanoantennas for tunable organic plasmonics. Communications Materials, 2022, 3, .	2.9	9
103	Europium doping of zincblende GaN by ion implantation. Journal of Applied Physics, 2009, 105, 113507.	1.1	8
104	Cavity-enhanced optical Hall effect in epitaxial graphene detected at terahertz frequencies. Applied Surface Science, 2017, 421, 357-360.	3.1	8
105	N-polar AlN nucleation layers grown by hot-wall MOCVD on SiC: Effects of substrate orientation on the polarity, surface morphology and crystal quality. Physica B: Condensed Matter, 2020, 580, 411819.	1.3	8
106	Ti thin films deposited by high-power impulse magnetron sputtering in an industrial system: Process parameters for a low surface roughness. Vacuum, 2022, 195, 110698.	1.6	8
107	Impact of in situ NH3 pre-treatment of LPCVD SiN passivation on GaN HEMT performance. Semiconductor Science and Technology, 2022, 37, 035011.	1.0	8
108	Terahertz electron paramagnetic resonance generalized spectroscopic ellipsometry: The magnetic response of the nitrogen defect in 4H-SiC. Applied Physics Letters, 2022, 120, .	1.5	8

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109	Strain Evolution in High Temperature AlN Buffer Layers for HVPE-GaN Growth. Physica Status Solidi A, 2002, 190, 59-64.	1.7	7
110	In-plane epitaxial relationships between a-plane sapphire substrates and GaN layers grown by different techniques. Journal of Crystal Growth, 2003, 257, 1-6.	0.7	7
111	Correlation between switching to n-type conductivity and structural defects in highly Mg-doped InN. Applied Physics Letters, 2015, 106, 232102.	1.5	7
112	Very High Growth Rate of 4H-SiC Using MTS as Chloride-Based Precursor. Materials Science Forum, 0, 600-603, 115-118.	0.3	6
113	Electron effective mass in In0.33Ga0.67N determined by mid-infrared optical Hall effect. Applied Physics Letters, 2018, 112, .	1.5	6
114	Infrared active phonons in monoclinic lutetium oxyorthosilicate. Journal of Applied Physics, 2020, 127, .	1.1	6
115	Anisotropy of the In-Plane Strain in GaN Grown on A-Plane Sapphire. Physica Status Solidi (B): Basic Research, 2002, 234, 892-896.	0.7	5
116	Characterization of mass-transport grown GaN by hydride vapour-phase epitaxy. Journal of Crystal Growth, 2004, 273, 118-128.	0.7	5
117	Phonons in strained AlGaN/GaN superlattices. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 170-174.	0.8	5
118	Optimization of GaN Nanowires Reformation Process by Metalorganic Chemical Vapor Deposition for Deviceâ€Quality GaN Templates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900581.	0.7	5
119	Brillouin zone center phonon modes in ZnGa2O4. Applied Physics Letters, 2020, 117, .	1.5	5
120	Tunable Structural Color Images by UVâ€Patterned Conducting Polymer Nanofilms on Metal Surfaces (Adv. Mater. 33/2021). Advanced Materials, 2021, 33, 2170261.	11.1	5
121	On the polarity determination and polarity inversion in nitrogen-polar group III-nitride layers grown on SiC. Journal of Applied Physics, 2022, 131, .	1.1	5
122	Optical properties of undoped AlN/GaN superlattices grown by metalorganic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2614-2617.	0.8	4
123	Assessment of phonon mode characteristics via infrared spectroscopic ellipsometry ona-plane GaN. Physica Status Solidi (B): Basic Research, 2006, 243, 1594-1598.	0.7	4
124	Optical properties of GaAs0.9-xNxSb0.1 alloy films studied by spectroscopic ellipsometry. Thin Solid Films, 2011, 519, 2838-2842.	0.8	4
125	Unintentional incorporation of H and related structural and freeâ€electron properties of câ€and aâ€plane InN. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 91-94.	0.8	4
126	(Invited) Challenges of Graphene Growth on Silicon Carbide. ECS Transactions, 2013, 53, 9-16.	0.3	4

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127	Free-charge carrier parameters of n-type, p-type and compensated InN:Mg determined by infrared spectroscopic ellipsometry. Thin Solid Films, 2014, 571, 384-388.	0.8	4
128	Origin of layer decoupling in ordered multilayer graphene grown by high-temperature sublimation on C-face 4H-SiC. APL Materials, 2020, 8, .	2.2	4
129	Morphology of Thin Films of Aromatic Ellagic Acid and Its Hydrogen Bonding Interactions. Journal of Physical Chemistry C, 2020, 124, 16381-16390.	1.5	4
130	Resolving mobility anisotropy in quasi-free-standing epitaxial graphene by terahertz optical Hall effect. Carbon, 2021, 172, 248-259.	5.4	4
131	Infrared-active phonon modes and static dielectric constants in Î±-(AlxGa1â^'x)2O3 (0.18â€‰â‰€â€‰xâ€‰â‰€â€‰0.54) alloys. Applied Physics Letters, 2022, 120, .	1.5	4
132	Microhardness characterization of structures obtained by ironâ€“silicon solid-state reaction. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 78, 131-134.	1.7	3
133	Title is missing!. Journal of Materials Science, 2001, 36, 1951-1956.	1.7	3
134	Generalized infrared ellipsometry study of thin epitaxial AlN layers with complex strain behavior. Physica B: Condensed Matter, 2003, 340-342, 416-420.	1.3	3
135	Grazing incident asymmetric X-ray diffraction of Î²-FeSi2 layers, produced by ion beam synthesis. Vacuum, 2004, 76, 277-280.	1.6	3
136	Bending in HVPE GaN free-standing films: effects of laser lift-off, polishing and high-pressure annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1475-1478.	0.8	3
137	Strain and compositional analyses of Alâ€rich Al_{1â€“x}In_xN films grown by MOVPE: impact on the applicability of Vegard's rule. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1859-1862.	0.8	3
138	Unintentional incorporation of hydrogen in wurtzite InN with different surface orientations. Journal of Applied Physics, 2011, 110, .	1.1	3
139	Terahertz optical properties of polymethacrylates after thermal annealing. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 062924.	0.6	3
140	Critical View on Buffer Layer Formation and Monolayer Graphene Properties in High-Temperature Sublimation. Applied Sciences (Switzerland), 2021, 11, 1891.	1.3	3
141	Linear strain and stress potential parameters for the three fundamental band to band transitions in Î² -Ga2O3. Applied Physics Letters, 2022, 120, .	1.5	3
142	Enhancement of 2DEG effective mass in AlN/Al0.78Ga0.22N high electron mobility transistor structure determined by THz optical Hall effect. Applied Physics Letters, 2022, 120, .	1.5	3
143	DAP emission band in a carbon doped (1â€101)GaN grown on (001)Si substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S772.	0.8	2
144	Atomic layer deposition of Al2O3on NF3-pre-treated graphene. , 2015, , .		2

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145	Mass Transport Growth and Properties of Hydride Vapour Phase Epitaxy GaN. Physica Status Solidi A, 2001, 188, 447-451.	1.7	1
146	Effect of rapid thermal annealing on the structure of ion beam synthesized Î²-FeSi2. Vacuum, 2002, 69, 449-454.	1.6	1
147	High pressure annealing of HVPE GaN free-standing films: redistribution of defects and stress. Materials Research Society Symposia Proceedings, 2004, 831, 49.	0.1	1
148	Optical investigation of AlGaN/GaN quantum wells and superlattices. Physica Status Solidi A, 2004, 201, 2251-2258.	1.7	1
149	Optical properties of InN/In_{0.73}Ga_{0.27}N multiple quantum wells studied by spectroscopic ellipsometry. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1629-1632.	0.8	1
150	A Double Scattering Analytical Model For Elastic Recoil Detection Analysis. , 2011, , .		1
151	Hydrogen In Group-III Nitrides: An Ion Beam Analysis Study. , 2011, , .		1
152	Spectroscopic Mapping Ellipsometry of Graphene Grown on 3C SiC. Materials Research Society Symposia Proceedings, 2012, 1407, 99.	0.1	1
153	Recombination processes in Mg doped wurtzite InN films with p- and n-type conductivity. AIP Advances, 2019, 9, 015114.	0.6	1
154	Anisotropy of the In-Plane Strain in GaN Grown on A-Plane Sapphire. , 2002, 234, 892.		1
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